

TECHNICAL DATA
DATA SHEET 1063, REV. B

HERMETIC POWER MOSFET N-CANNEL

FEATURES:

- 100 Volt, 0.035 Ohm, 55A MOSFET
- Electrically Isolated, Hermetically Sealed
- Electrically Equivalent to OM55N10SA

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	± 20	Volts
CONTINUOUS DRAIN CURRENT ^① $V_{GS}=10\text{V}$, $T_C = 25^\circ\text{C}$ $V_{GS}=10\text{V}$, $T_C = 100^\circ\text{C}$	I_D	-	-	55 33	Amps
PULSED DRAIN CURRENT ^② @ $T_C = 25^\circ\text{C}$	I_{DM}	-	-	180	Amps
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	$^\circ\text{C}$
TERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-	0.43	$^\circ\text{C}/\text{W}$
TOTAL DEVICE DISSIPATION @ $T_C = 25^\circ\text{C}$	P_D	-	-	290	Watts

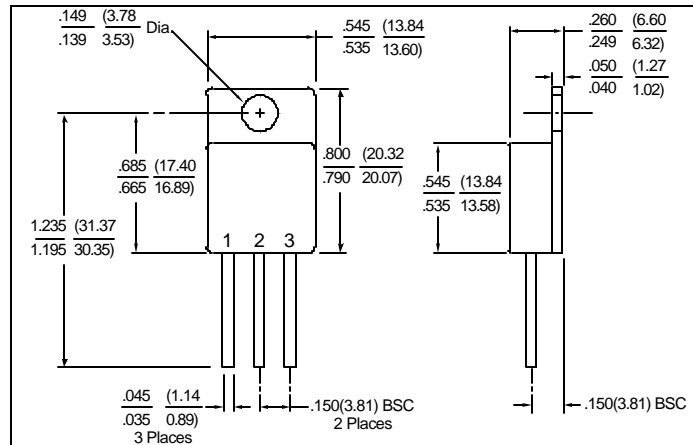
ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE $V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$	BV_{DSS}	100	-	-	Volts
DRAIN TO SOURCE ON STATE RESISTANCE $V_{GS} = 10\text{V}$, $I_D = 30 \text{ Adc}$ $T_C = 100^\circ\text{C}$	$R_{DS(ON)}$	-	-	0.035 0.07	Ω
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	$V_{GS(th)}$	2.0	-	4.0	Volts
FORWARD TRANSCONDUCTANCE $V_{DS} > I_{D(on)}$, $I_D = 30 \text{ Adc}$	g_{fs}	25	-	-	$\text{S}(1/\Omega)$
ZERO GATE VOLTAGE DRAIN CURRENT $V_{DS} = \text{Max. Rating}$, $V_{GS} = 0\text{V}$ $V_{DS} = \text{Max. Rating} \times 0.8$ $V_{GS} = 0\text{V}$, $T_J = 125^\circ\text{C}$	I_{DSS}	-	-	250 1000	μA
GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = -20\text{V}$ GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = 20\text{V}$	I_{GSS}	-	-	-100 100	nA
TOTAL GATE CHARGE $V_{GS} = 10\text{V}$, $V_{DS} = \text{Max. Rating} \times 0.8$, $I_D = 30\text{A}$	Q_g	-	120	-	nC
OFF VOLTAGE RISE TIME FALL TIME CROSSOVER TIME $V_{DD} = 80\text{V}$, $I_D = 30\text{A}$, $R_G = 50\Omega$, $V_{GS} = 10\text{V}$	$T_{r(Voff)}$ t_f t_{cross}	-	200 210 410	-	nsec
DIODE FORWARD VOLTAGE $T_J = 25^\circ\text{C}$, $I_{SD} = 55\text{A}$, $V_{GS} = 0\text{V}$ $T_J = 125^\circ\text{C}$	V_{SD}	-	-	1.5	Volts
DIODE REVERSE RECOVERY TIME REVERSE RECOVERY CHARGE $T_J = 25^\circ\text{C}$, $I_S = 55\text{A}$, $diS/dt = -100\text{A}/\mu\text{sec}$ $V_R = 80 \text{ V}$	t_{rr} Q_{rr}	-	180 1.8	-	nsec μC
INPUT CAPACITANCE OUTPUT CAPACITANCE REVERSE TRANSFER CAPACITANCE $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1.0\text{MHz}$	C_{iss} C_{oss} C_{rss}	-	4000 1100 250	-	pF

① Package Limited: $I_D = 25\text{A}$ @ 25°C ② Pulse Test: Pulse width 300 μs . Duty Cycle 1.5%

SENSITRON
DATA SHEET 1063
REVISION B

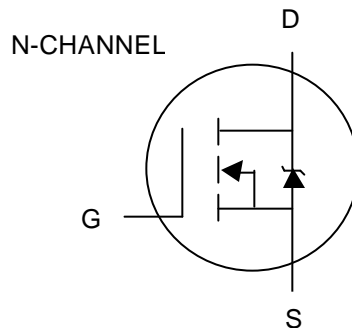
MECHANICAL DIMENSIONS: in Inches / mm



TO-254

DEVICE TYPE	PIN-1	PIN-2	PIN-3
N-CHANNEL MOSFET TO-254 PACKAGE	DRAIN	SOURCE	GATE

SCHEMATIC SYMBOL



TECHNICAL DATA

DISCLAIMER:

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.